

AMENDMENTS TO THE SPECIFICATION

Please amend the title of the application as follows:

SEED CRYSTAL CONSISTING OF SILICON CARBIDE SINGLE CRYSTAL AND
METHOD FOR PRODUCING INGOT USING THE SAME

Please replace the fourth paragraph on page 4 with the
following amended paragraph:

Polytype of silicon carbide single crystal is almost
determined by face polarity of a {0001} ~~both-type~~ face crystal
used for crystal growth. Regarding the {0001} face, there are
two kinds of the (0001) Si face and the (000-1) C face which
are different in polarity, and the outermost surfaces of
respective faces are covered with a silicon atom layer and a
carbon atom layer. A word {0001} is a generic term of these
two faces.

Please replace the first paragraph on page 13 with the
following amended paragraph:

Note that the angle inclined with respect to a (11-20) face of
the single crystal growing face is called "off-angle" and a
direction introducing the off-angle is called "off-direction"
in the following explanation. As shown in FIG. 3, the off-
direction is in the plane including the directions <0001> and
[1-100], and the normal line of the single crystal growing
face is in the plane including the off-direction and the ~~<11-
20>~~ [11-20] direction.

Please replace the third paragraph on page 15 with the
following amended paragraph:

When the angle β is 45 degrees or more and 135 degrees or
less, or when it is -135 degrees or more and -45 degrees or
less, the off-direction comes to be nearer to the ~~<1-100>~~
[1-100] direction than the <0001> direction. Between this
case and the case where the off-direction comes to be near to
the <0001> direction, the structure of the steps and the like

differ from each other. And when the off-direction comes near to the $\langle 1-100 \rangle$ [1-100] direction, arbitrariness remains in an adsorption arrangement of silicon carbide molecules in the step so that a stacking fault can be generated. Therefore, the off-direction is required to be a direction inclined by - 45 degrees or more and 45 degrees or less from a $\langle 0001 \rangle$ direction to the [1-100] direction.

Please replace the second paragraph on page 33 with the following amended paragraph:

Using the crystal growth system shown in FIG. 6, a silicon carbide single crystal was produced. Specifically, first, a wafer was cut from a 4H-type silicon carbide single crystal which had grown in the $[000-1]$ C direction. At this time, the silicon carbide single crystal in which micropipe defects were contained but no stacking faults existed was used. Regarding the cut face, a face inclined at an angle of 10 degrees with respect to the $(11-20)$ face of the silicon carbide single crystal in the $[0001]$ Si direction was taken as the cut face ($\alpha = 10^\circ$, $\beta = 0^\circ$). Incidentally, the deviation of the off-direction from the ~~$\{000-1\}$ Si~~ $[0001]$ Si direction was set to be within $\pm 1^\circ$.